

semiconductor device, using the thin photoresist layer as a mask.

Utilizing this thin photoresist layer, taking into account other height variables, the source and drain regions can be opened only as needed. At a 45° angle, the implant can be delivered to all transistors in the circuit in the targeted area as well as getting only a large amount of the dose (up to ¾ of the dose) to the transistor edge which sits on the trench edge.